

Abstract

Method, control system and plant for processing a semiconductor wafer, and semiconductor wafer

The invention relates to a method of processing a semiconductor wafer (600), comprising three processing operations, namely a first polishing operation in which the semiconductor wafer (600) is subjected to double-sided polishing, followed by a second polishing operation in which the semiconductor wafer (600) is subjected to chemical-mechanical polishing, and followed by a coating operation in which the semiconductor wafer (600) is subjected to epitaxial deposition of a layer. The invention further relates to a control system for conducting the method, to a plant for processing a semiconductor wafer comprising the control system, and to a semiconductor wafer. It is a feature of the method that at least one operating parameter for each of the three processing operations is defined in the respective processing operation, specifically

based on at least one wafer parameter which is determined on the semiconductor wafer to be processed;

based on an actual state of a processing apparatus with which the respective processing operation is conducted; and

based on an optimization of wafer parameters for characterization of flatness with regard to the condition thereof after undergoing the three processing operations instead of an optimization of these wafer parameters with regard to the condition thereof after every individual processing step of the three.

Drawing relating to abstract: fig. 9